

NSS35200CF8T1G

35 V, 7 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- This is a Pb-Free Device

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-35	Vdc
Collector-Base Voltage	V_{CBO}	-55	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-2.0	Adc
Collector Current - Peak	I_{CM}	-7.0	A
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	635	mW
		5.1	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	200	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	1.35	W
		11	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	90	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Lead #1	$R_{\theta JL}$	15	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 sec)	$P_{D\text{single}}$ (Notes 2 & 3)	2.75	W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- FR-4 @ 100 mm², 1 oz copper traces.
- FR-4 @ 500 mm², 1 oz copper traces.
- Thermal response.

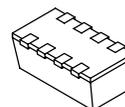
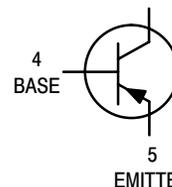


ON Semiconductor[®]

<http://onsemi.com>

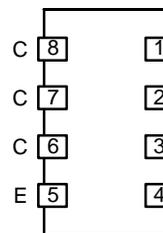
35 VOLTS
7.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 78 m Ω

COLLECTOR
1, 2, 3, 6, 7, 8

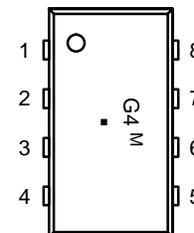


ChipFET™
CASE 1206A
STYLE 4

PIN CONNECTIONS



MARKING DIAGRAM



G4 = Specific Device Code
M = Month Code
■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NSS35200CF8T1G	ChipFET (Pb-Free)	3000/ Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSS35200CF8T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = -10 mA _{dc} , I _B = 0)	V _{(BR)CEO}	-35	-45	-	V _{dc}
Collector–Base Breakdown Voltage (I _C = -0.1 mA _{dc} , I _E = 0)	V _{(BR)CBO}	-55	-65	-	V _{dc}
Emitter–Base Breakdown Voltage (I _E = -0.1 mA _{dc} , I _C = 0)	V _{(BR)EBO}	-5.0	-7.0	-	V _{dc}
Collector Cutoff Current (V _{CB} = -35 V _{dc} , I _E = 0)	I _{CBO}	-	-0.03	-0.1	μA _{dc}
Collector–Emitter Cutoff Current (V _{CES} = -35 V _{dc})	I _{CES}	-	-0.03	-0.1	μA _{dc}
Emitter Cutoff Current (V _{EB} = -6.0 V _{dc})	I _{EBO}	-	-0.01	-0.1	μA _{dc}
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I _C = -1.0 A, V _{CE} = -2.0 V) (I _C = -1.5 A, V _{CE} = -2.0 V) (I _C = -2.0 A, V _{CE} = -2.0 V)	h _{FE}	100 100 100	200 200 200	- 400 -	
Collector–Emitter Saturation Voltage (Note 4) (I _C = -0.1 A, I _B = -0.010 A) (I _C = -1.0 A, I _B = -0.010 A) (I _C = -2.0 A, I _B = -0.02 A)	V _{CE(sat)}	- - -	- - -	-0.10 -0.15 -0.30	V
Base–Emitter Saturation Voltage (Note 4) (I _C = -1.0 A, I _B = -0.01 A)	V _{BE(sat)}	-	-0.68	-0.85	V
Base–Emitter Turn-on Voltage (Note 4) (I _C = -2.0 A, V _{CE} = -3.0 V)	V _{BE(on)}	-	-0.81	-0.875	V
Cutoff Frequency (I _C = -100 mA, V _{CE} = -5.0 V, f = 100 MHz)	f _T	100	-	-	MHz
Input Capacitance (V _{EB} = -0.5 V, f = 1.0 MHz)	C _{ibo}	-	600	650	pF
Output Capacitance (V _{CB} = -3.0 V, f = 1.0 MHz)	C _{obo}	-	85	100	pF
Turn-on Time (V _{CC} = -10 V, I _{B1} = -100 mA, I _C = -1 A, R _L = 3 Ω)	t _{on}	-	35	-	nS
Turn-off Time (V _{CC} = -10 V, I _{B1} = I _{B2} = -100 mA, I _C = 1 A, R _L = 3 Ω)	t _{off}	-	225	-	nS

4. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

NSS35200CF8T1G

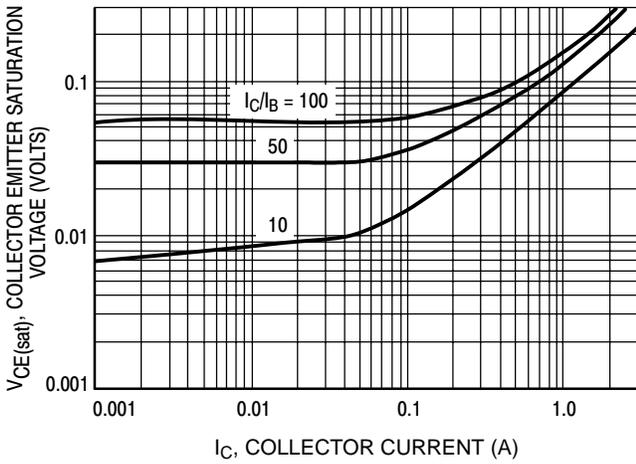


Figure 1. Collector Emitter Saturation Voltage versus Collector Current

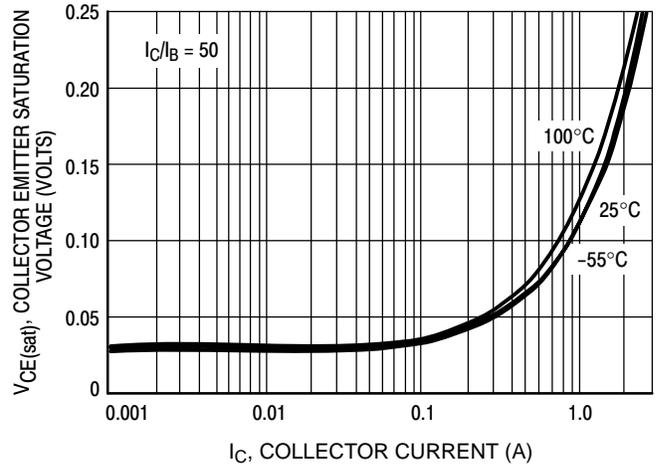


Figure 2. Collector Emitter Saturation Voltage versus Collector Current

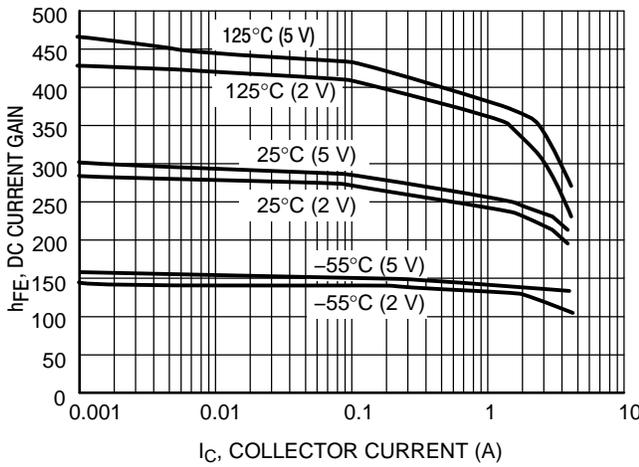


Figure 3. DC Current Gain versus Collector Current

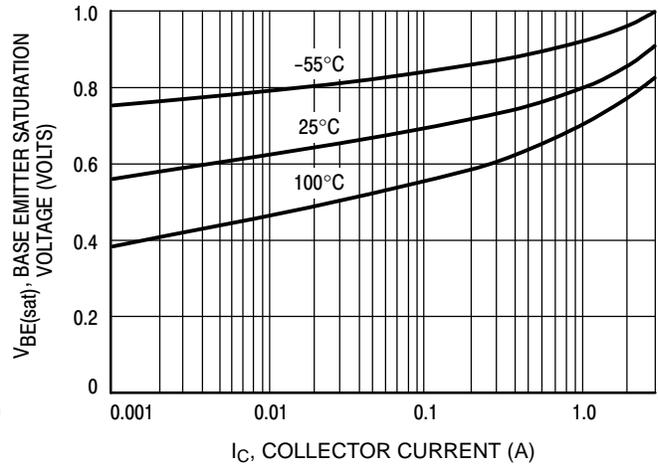


Figure 4. Base Emitter Saturation Voltage versus Collector Current

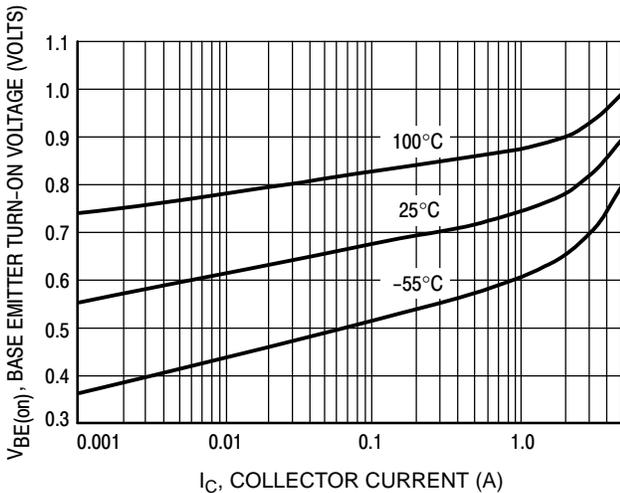


Figure 5. Base Emitter Turn-On Voltage versus Collector Current

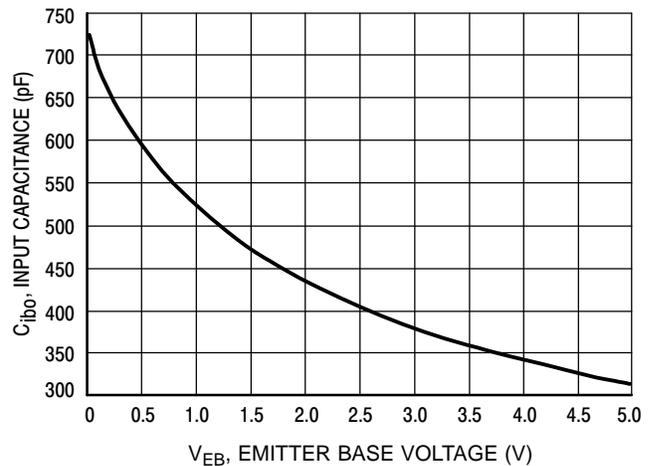


Figure 6. Input Capacitance

NSS35200CF8T1G

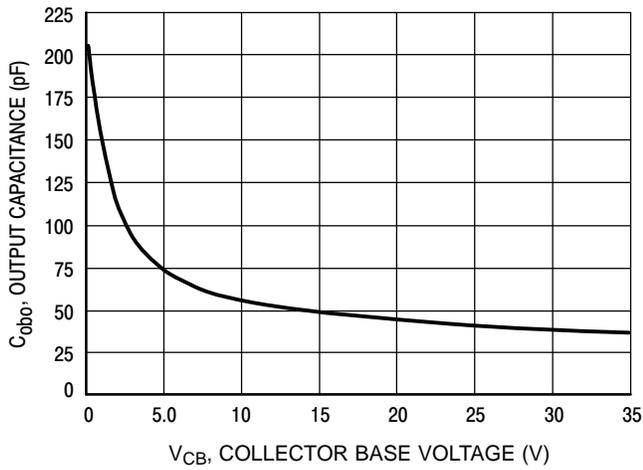


Figure 7. Output Capacitance

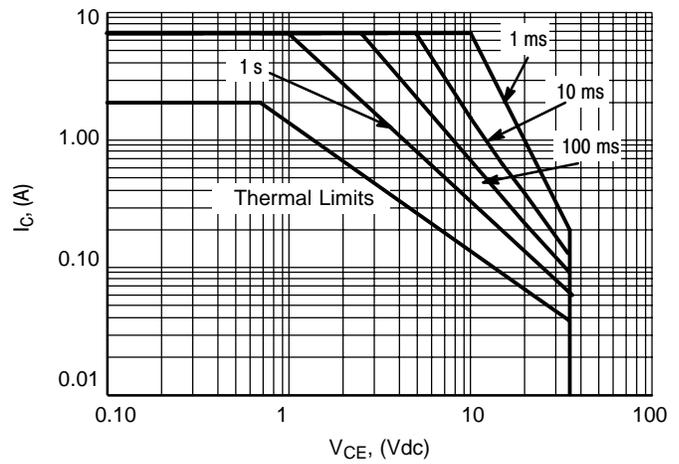


Figure 8. Safe Operating Area

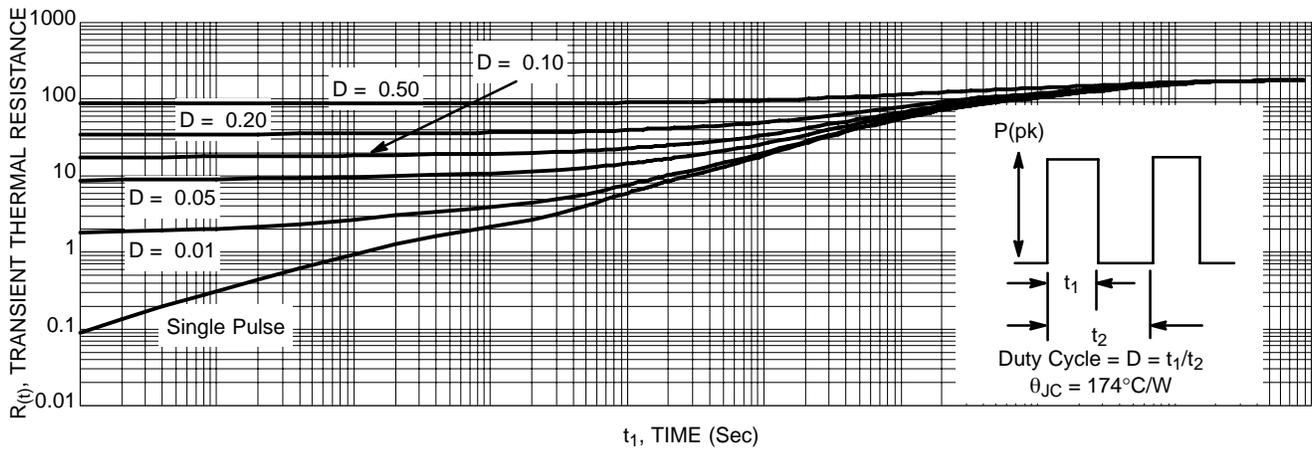
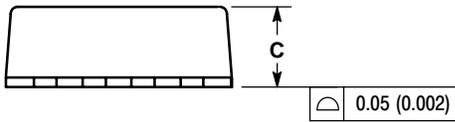
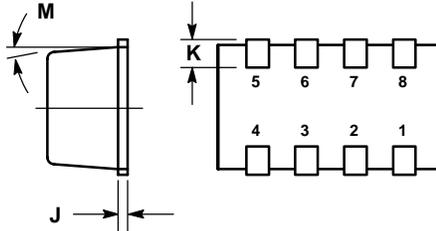
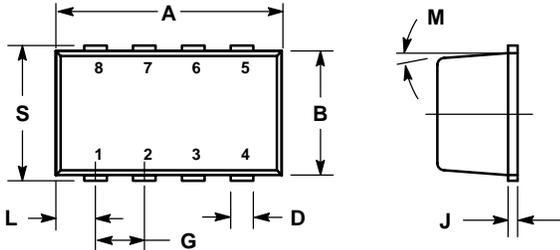


Figure 9. Normalized Thermal Response

NSS35200CF8T1G

PACKAGE DIMENSIONS

ChipFET
CASE 1206A-03
ISSUE PRELIMINARY



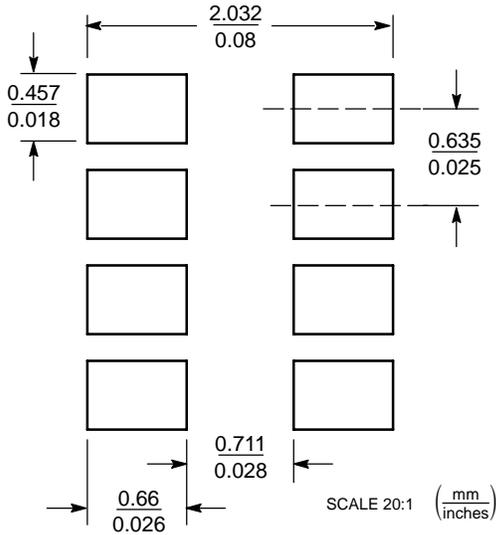
STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. COLLECTOR
4. BASE
5. EMITTER
6. COLLECTOR
7. COLLECTOR
8. COLLECTOR

NOTES:

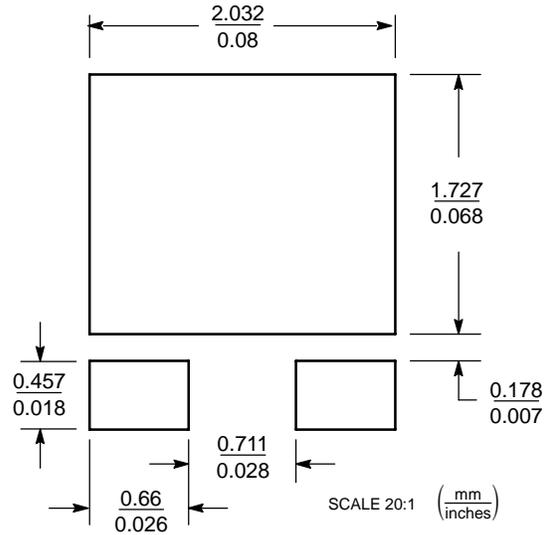
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5° NOM		5° NOM	
S	1.80	2.00	0.072	0.080

SOLDERING FOOTPRINT*



Basic



Style 4

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NSS35200CF8T1G

ChipFET is a trademark of Vishay Siliconix.

ON Semiconductor and **ON** are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your
local Sales Representative.

NSS35200CF8T1G/D